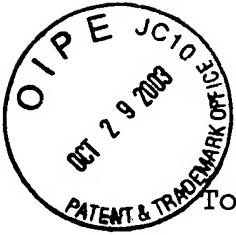


TSMC-03-424



October 24, 2003

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/627,795 07/25/03

Yi-Chen Chen et al.

BARRIER-SLURRY-FREE COPPER
CMP PROCESS

Grp. Art Unit:

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on October 27, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 10/27/03

U.S. Patent 6,217,416 to Kaufman et al., "Chemical Mechanical Polishing Slurry Useful for Copper/Tantalum Substrates," describes a first and second CMP slurry wherein the second slurry includes an abrasive an oxidizing agent and acetic acid wherein the weight ratio of oxidizing agent/acetic agent is at least 10 and wherein the two slurries are sequentially used in a method to polish a substrate containing copper and containing tantalum or tantalum oxide or both tantalum and tantalum oxide.

U.S. Patent 6,338,744 to Tateyama et al., "Polishing Slurry and Polishing Method," describes a high purity polishing slurry comprising water and dispersed silica particles.

U.S. Patent 6,261,158 to Holland et al., "Multi-Step Chemical Mechanical Polishing," describes a multi-step CMP system used to polish a wafer to form metal interconnects in a dielectric layer upon which barrier and metal layers have been formed.

U.S. Patent 6,447,371 to Brusic Kaufman et al., "Chemical Mechanical Polishing Slurry Useful for Copper/Tantalum Substrates," describes a chemical mechanical polishing slurry useful for copper/tantalum substrates.

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U.S. Patent 6,313,039 to Small et al., "Chemical Mechanical Polishing Composition and Process," describes a chemical mechanical polishing composition and process.

U.S. Patent 6,530,968 to Tsuchiya et al., "Chemical Mechanical Polishing Slurry," describes a chemical mechanical polishing slurry.

Sincerely,

A handwritten signature in black ink, appearing to read 'SBA', with a large, stylized loop at the end.

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)	Doc. Number (Sequence) ISMC-03-424	Application Number 10/627,795
	Applicant Yi-Chen Chen et al.	
	Filing Date 07/25/03	Drawing Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	NUM. DATE IF APPROPRIATE
	6217416	4/17/01	Kaufman et al.	451	41	6/26/98
	6338744	1/15/02	Tateyama et al.	51	308	1/11/00
	6261158	7/17/01	Holland et al.	451	63	12/16/98
	6447371	9/10/02	Brusic Kaufman et al.	451	36	3/6/01
	6313039	11/6/01	Small et al.	438	693	1/11/00
	6530968	3/11/03	Tsuchiya et al.	51	307	11/20/01

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

